



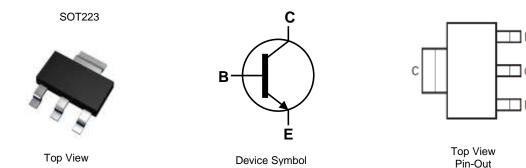
300V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 300V
- I_C = 3.5A High Continuous Collector Current
- I_{CM} = 5A Peak Pulse Current
- Very Low Saturation Voltage V_{CE(SAT)} < 155mV @ 1A
- R_{CE(SAT)} = 87mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 3A for a High Gain Hold-Up
- Complementary PNP Type: FZT957
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)



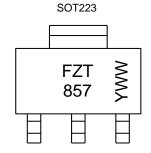
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT857TA	AEC-Q101	FZT857	7	12	1,000
FZT857QTA	Automotive	FZT857	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



FZT 857 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 7 = 2017) WW or $\overline{W}W$ = Week Code (01–53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	350	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	3.5	Α
Peak Pulse Current	I _{CM}	5	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		3.0 24	W	
Linear Derating Factor	(Note 7)	P _D	1.6 12.8	mW/°C	
Thermal Desistance Junction to Ambient	(Note 6)	R _{0JA}	42		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	78	°C/W	
Thermal Resistance Junction to Lead (Note 8)		R _{0JL}	8.8		
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

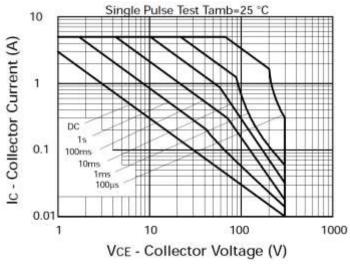
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

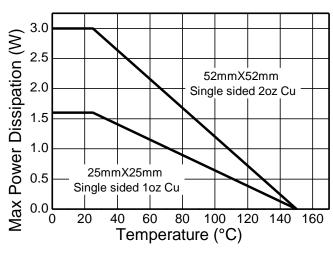
Notes:

- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



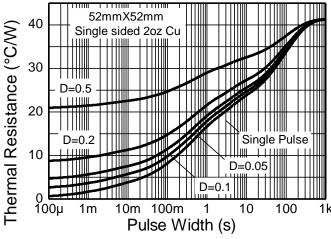
Thermal Characteristics and Derating Information

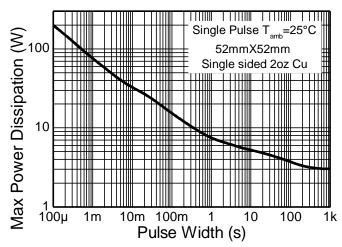




Safe Operating Area







Transient Thermal Impedance

Pulse Power Dissipation



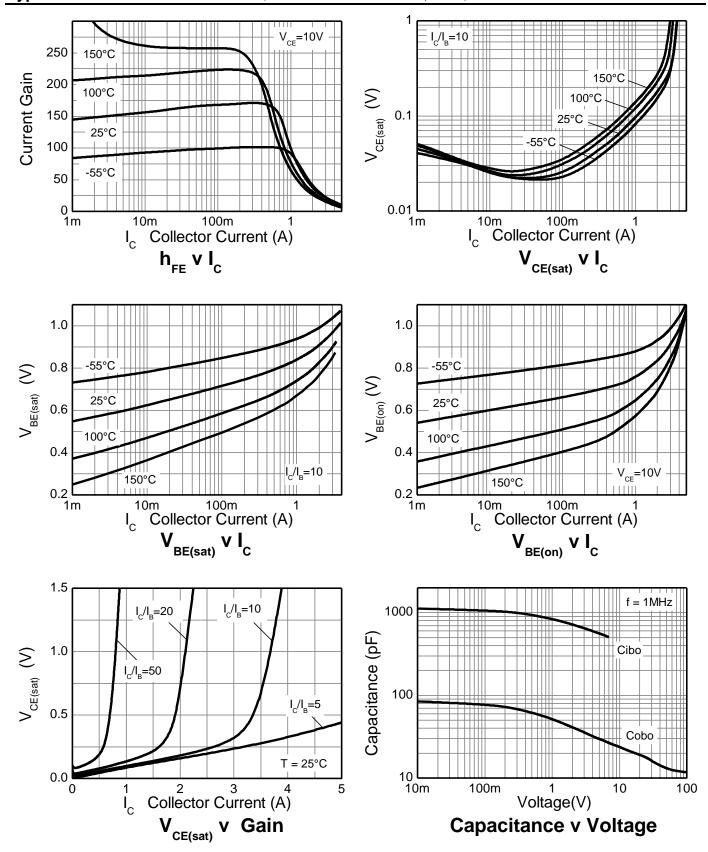
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	350	475	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	350	475	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	300	350	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV_EBO	7	8	_	V	$I_E = 100\mu A$
Collector Cut-Off Current	I _{CBO}	_	<1 —	50 1	nΑ μΑ	V _{CB} = 300V V _{CB} = 300V, T _A = +100°C
Collector Cut-Off Current	I _{CER}	_	<1 —	50 1	nΑ μΑ	$V_{CE} = 300V, R_B \le 1k\Omega$ $V_{CE} = 300V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	I _{EBO}	_	<1	10	nA	$V_{EB} = 6V$
		100	200	_	ı	$I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$
DC Current Gain (Note 10)	h _{FE}	100	200	300		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$
DC Current Gain (Note 10)		15	25	_		$I_C = 2A$, $V_{CE} = 10V$
		_	15	_		$I_C = 3A$, $V_{CE} = 10V$
	V _{CE(SAT)}	_	59	100		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)		_	95	155	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emilier Saturation Voltage (Note 10)		_	180	230	IIIV	$I_C = 2A$, $I_B = 200mA$
		_	300	345		$I_C = 3.5A$, $I_B = 600mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	1,020	1,250	mV	$I_C = 3.5A$, $I_B = 600mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	_	940	1,120	mV	$I_C = 3.5A, V_{CE} = 10V$
Current Gain-Bandwidth Product (Note 10)	f⊤	_	80	_	MHz	$I_{C} = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 50 MHz
Output Capacitance	C_OBO	_	21	_	pF	$V_{CB} = 20V$, $f = 1MHz$
Switching Times	t _{ON}	_	100	_	ns	$I_C = 250 \text{mA}, V_{CC} = 50 \text{V},$
Owitering Titles	toff	_	5,300	_	110	$I_{B1} = -I_{B2} = 25mA$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

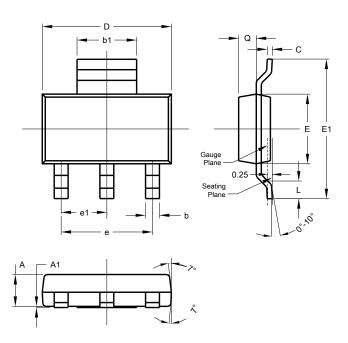




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

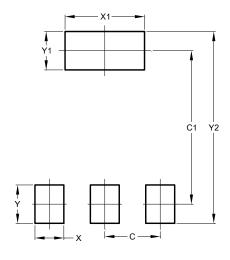


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

March 2017

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